

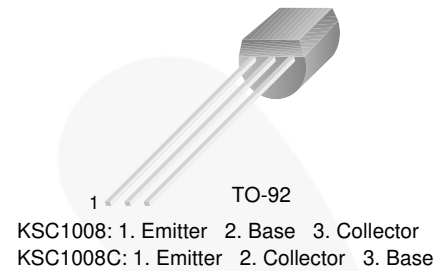


November 2014

KSC1008 NPN Epitaxial Silicon Transistor

Features

- Low-Frequency Amplifier Medium Speed Switching
- High Collector-Base Voltage : $V_{CBO} = 80\text{ V}$
- Collector Current : $I_C = 700\text{ mA}$
- Suffix “-C” means Center Collector (1. Emitter 2. Collector 3. Base)
- Non Suffix “-C” means Side Collector (1. Emitter 2. Base 3. Collector)
- Complement to KSA708



Ordering Information⁽¹⁾

Part Number	Top Mark	Package	Packing Method
KSC1008OBU	C1008 O-	TO-92 3L	Bulk
KSC1008YBU	C1008 Y-	TO-92 3L	Bulk
KSC1008YTA	C1008 Y-	TO-92 3L	Ammo, 2000 pcs
KSC1008CYTA	C1008 YC	TO-92 3L	Ammo, 2000 pcs
KSC1008GTA	C1008 G-	TO-92 3L	Ammo, 2000 pcs

Note:

1. Affix “-C-” means center collector pin. Affix “-O-, -Y-, -G-” means h_{FE} classification. Suffix “-BU” means bulk packing, straight lead form. Suffix “-TA” means tape and ammo packing, 0.200 in-line spacing lead form.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current	700	mA
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	-55 to 150	$^\circ\text{C}$

Thermal Characteristics⁽²⁾

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
P_D	Power Dissipation	800	mW
	Derate Above 25°C	6.4	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	156	$^\circ\text{C}/\text{W}$

Note:

2. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}$, $I_E = 0$	80			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}$, $I_B = 0$	60			V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}$, $I_C = 0$	8			V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 60 \text{ V}$, $I_E = 0$			0.1	μA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 5 \text{ V}$, $I_C = 0$			0.1	μA
h_{FE}	DC Current Gain	$V_{CE} = 2 \text{ V}$, $I_C = 50 \text{ mA}$	40		400	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$		0.2	0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$		0.86	1.10	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10 \text{ V}$, $I_C = 50 \text{ mA}$	30	50		MHz
C_{ob}	Output Capacitance	$V_{CB} = 10 \text{ V}$, $I_E = 0$, $f = 1 \text{ MHz}$		8		pF

h_{FE} Classification

Classification	R	O	Y	G
h_{FE}	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400

Typical Performance Characteristics

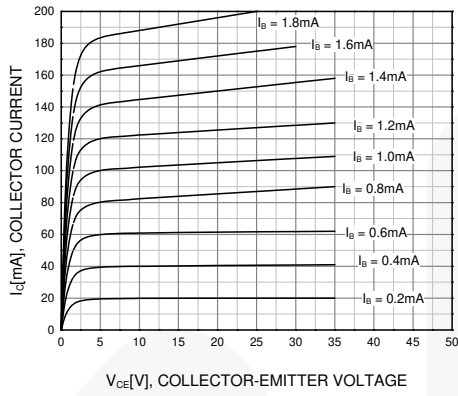


Figure 1. Static Characteristic

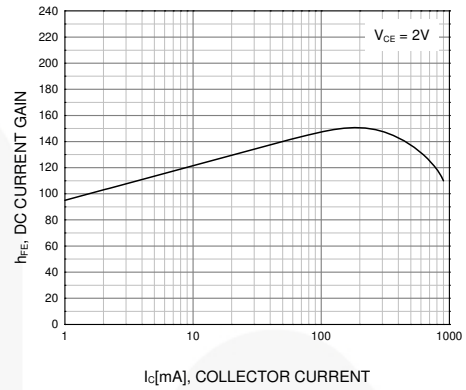


Figure 2. DC Current Gain

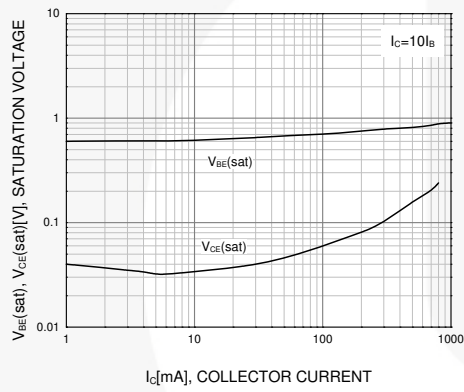


Figure 3. Base-Emitter Saturation Voltage and Collector-Emitter Saturation Voltage

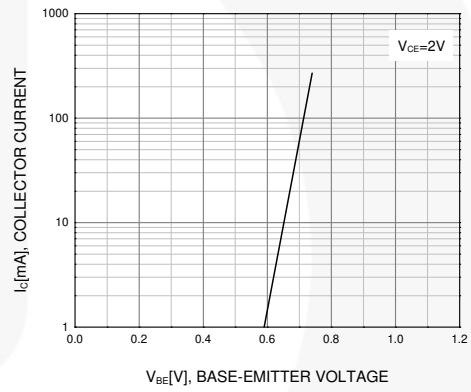


Figure 4. Base-Emitter On Voltage

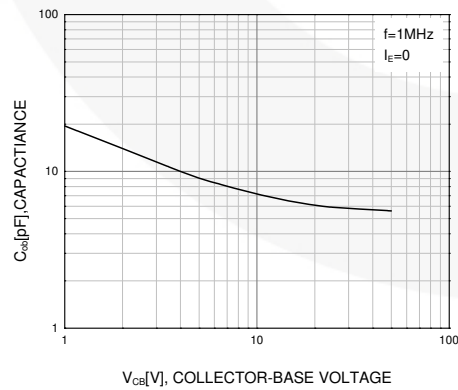
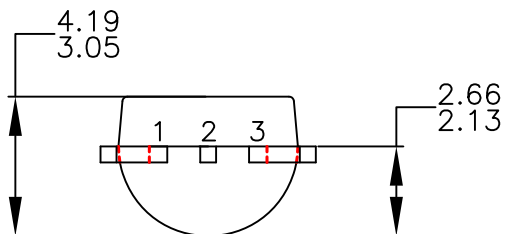
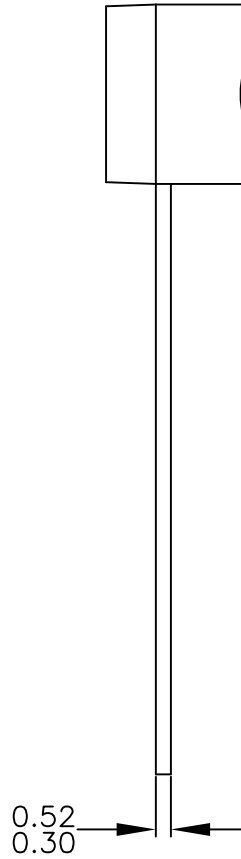
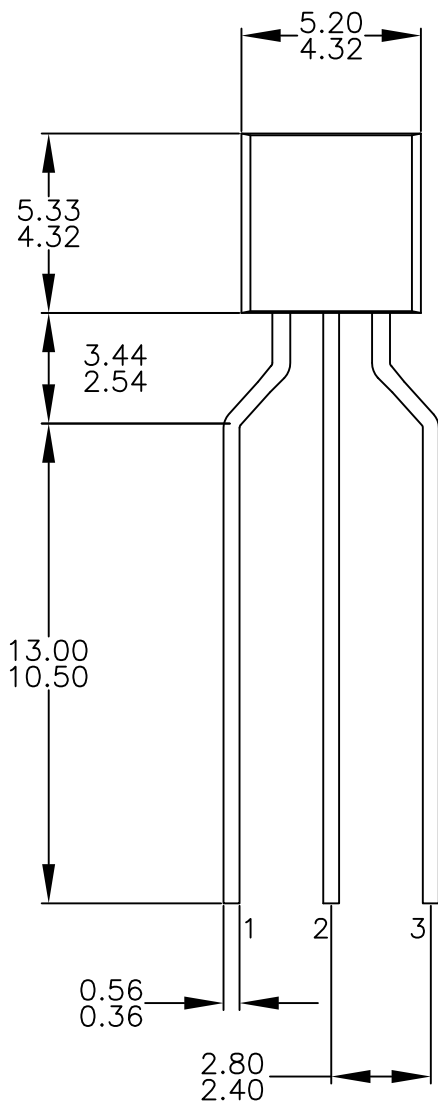
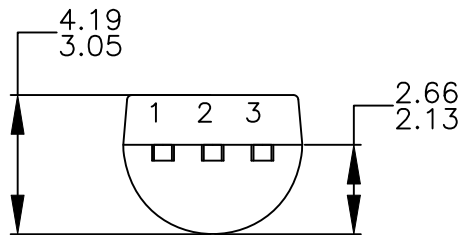
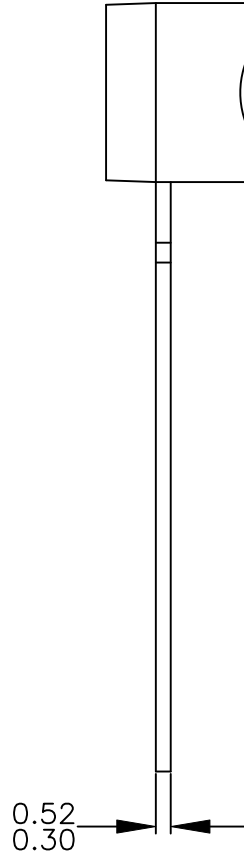
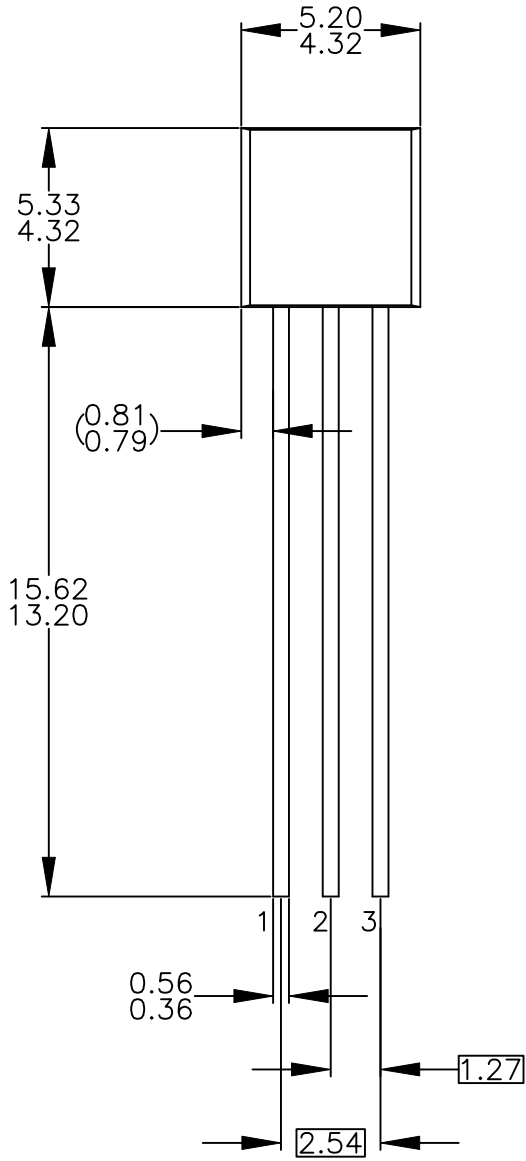


Figure 5. Collector Output Capacitance



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NOTES: UNLESS OTHERWISE SPECIFIED






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